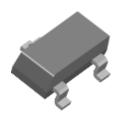
Analog Power AM1331P

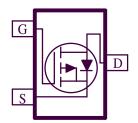
## P-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCTSUMMARY				
$V_{DS}(V)$	$\eta_{DS(on)}$ (OHM)	$I_D(A)$		
20	$0.112 @ V_{CS} = -10V$	-1.5		
-30	$0.172 @ V_{CS} = -4.5V$	-1.2		

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SC70-3 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS (TA = 25 °C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Maximum	Units		
Drain-Source Voltage		$V_{DS}$	-30	V		
Gate-Source Voltage		$V_{CS}$	±20	V		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	5°C I <sub>D</sub> -1.5 -1.2				
Continuous Drain Current	T <sub>A</sub> =70°C	1D	-1.2	A		
Pulsed Drain Current <sup>b</sup>	•	$I_{DM}$	-2.5			
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	±0.28	A		
D	T <sub>A</sub> =25°C	D	0.34	W		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C T <sub>A</sub> =70°C	FD	0.22	**		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
N	$t \le 5 \sec$	D	375	0000		
Maximum Junction-to-Ambient <sup>a</sup>	Steady-State	$R_{THJA}$	430			

1

## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)							
Downwoodow	CII	F . C . P.	Limits			T	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			±100	nA	
Zono Cata Valta da Drain Grunout	T	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zero Gate Voltage Drain Current	IDSS	IDSS $V_{DS} = -24 \text{ V}, V_{CS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-10	uA	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-5			Α	
A		$r_{DS(on)}$ $V_{GS} = -10 \text{ V, } I_D = -1.5 \text{ A}$ $V_{GS} = -4.5 \text{ V, } I_D = -1.2 \text{ A}$			112	mΩ	
Drain-Source On-Resistance <sup>A</sup>	IDS(on)				172		
Forward Tranconductance <sup>A</sup>	$g_{f_8}$	$V_{DS} = -5 \text{ V}, I_D = -1.5 \text{ A}$		9		S	
Diode Forward Voltage	V <sub>SD</sub>	$I_S = -0.46 A,  V_{GS} = 0 V$		-0.65		V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg	V 10X/X/ 5X/		7.2			
Gate-Source Charge	$Q_{2s}$	$V_{DS} = -10 \text{ V}, V_{GS} = -5 \text{ V},$ $I_{D} = -1.5 \text{ A}$		1.7		пC	
Gate-Drain Charge	$Q_{\rm gd}$	$I_D = -1.5 A$		1.5			
Tum-On Delay Time	t <sub>d(on)</sub>			10			
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, I_L = -1 \text{ A},$		9		ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN}$ =-4.5 V, $R_G$ =6 $\Omega$		27		1118	
Fall-Time	$t_{\mathrm{f}}$			11			

### Notes

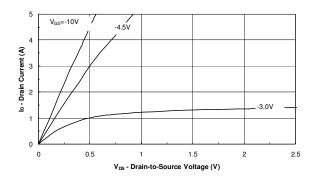
a. Pulse test: PW <= 300us duty cycle <= 2%.

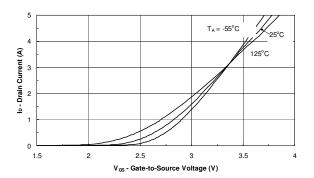
Guaranteed by design, not subject to production testing.

c. Repetitive rating, pulse width limited by junction temperature.

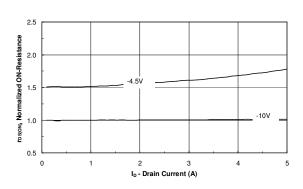
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## Typical Electrical Characteristics (P-Channel)

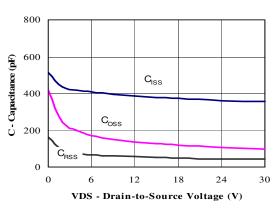




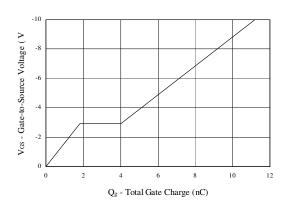
**Output Characteristics** 



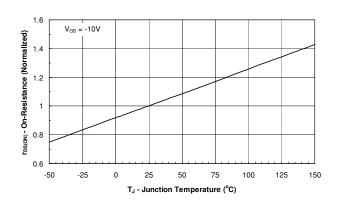
**Transfer Characteristics** 



On-Resistance vs. Drain Current



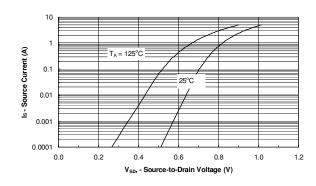
Capacitance

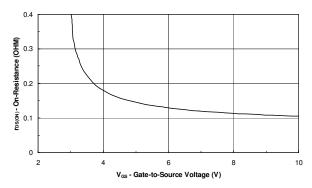


**Gate Charge** 

On-Resistance vs. Junction Temperature

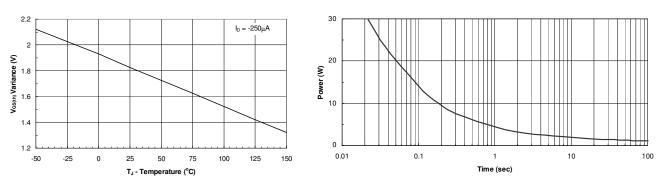
## Typical Electrical Characteristics (P-Channel)

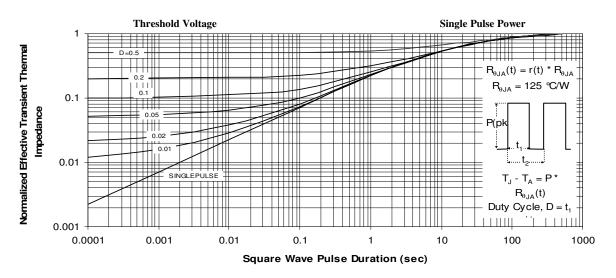




## Source-Drain Diode Forward Voltage

On-Resistance vs.Gate-to Source Voltage

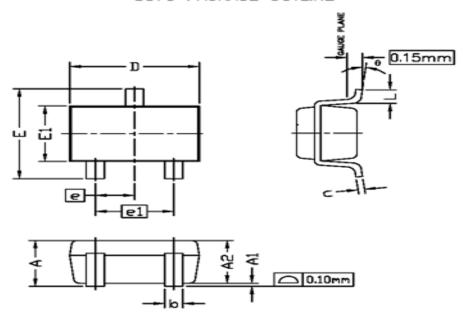




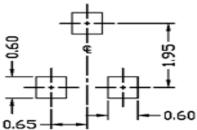
Normalized Thermal Transient Impedance, Junction-to-Ambient

# Package Information

SC70 PACKAGE OUTLINE



#### RECOMMENDED LAND PATTERN



				ENSIONS IN DR		
81 MBOLD	MIN	NOM	MAX	MIN	NOM	MAX
Α .			1.10			0.043
A1	0.00		0.10	0.00		0.004
A2	0.7	0.9	1.00	0.028	0.035	0.039
ь	0.15		0.30	0.006		0.012
¢	0.08		0.22	0.003		0.009
D	1.85	2.10	2,15	0.073	0.083	0.085
E	1.80	2.30	2,40	0.071	0.091	0.094
	0.65 BSC				0.026 BSC	
el	1.30 BSC				0.051 BSC	
E1	1.1	1.30	1.4	0.043	0.051	0.055
L	0.26	0.36	0.46	0.010	0.014	0.018
θ	0°	4°	8°	O <sub>o</sub>	4°	8°

UNIT: mm

#### NOTE

- 1. ALL DIMENSIONS ARE IN MILLMETERS.
- 2. DIMENSIONS ARE INCLUSIVE OF PLATING.
- PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
   MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 3 MILS EACH.
- DIE IS FACING UP FOR MOLD AND FACING DOWN FOR TRIM/FORM. ie: REVERSE TRIM/FORM.
- 5. DIMENSION L IS MEASURED IN GAUGE PLANE,
- CONTROLLING DIMENSION IS MILLIMETER.
- CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.